

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Masatake NAKANO, Kiyoshi MITANI  
and Shinichi TOMIZAWA

Application No.: US National Stage of PCT/JP00/06795

Filed: June 7, 2001

Docket No.: 109716

For: METHOD FOR PRODUCING BONDING WAFER AND BONDING WAFER

PRELIMINARY AMENDMENT

Director of the U.S. Patent and Trademark Office  
Washington, D. C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claims ~~1-9~~ without prejudice to or disclaimer of the subject matter contained therein.

Please add new claims 10-24 as follows:

10. A method for producing a bonding wafer by the hydrogen ion delamination method comprising at least a step of bonding a base wafer and a bond wafer having a micro bubble layer formed by gas ion implantation and a step of delaminating them at the micro bubble layer as a border, wherein a peripheral portion of a thin film formed on the base wafer is removed after the delamination step.--

11. The production method according to Claim 10, wherein the thin film has at least an SOI layer.--